

**AMENDMENTS TO THE SPECIFICATION**

Please amend the Specification as follows:

(1) Paragraph at page 5, lines 8-15.

The row-replacement circuit 30 has a test pad 31 to which a test signal RRT is applied. The pad 31 is pulled down to the ground voltage GND through a resistor 32 and is connected to an inverter 33. The output of the inverter 33 is connected to one input of a two-input NAND 34. To the other input of the NAND 34, control signal XR is applied which is activated and turned to be high level at the same time when the row-address signal RAD is activated. The output of the NAND 34 is connected to a node N1.

(2) Paragraph at page 6, line 24, through page 7 line 7.

The column switching circuit 70 has a test pad 71 to which a test signal CRT is applied. The pad 71 is pulled down to the ground voltage GND through a resistor 72 and connected to an inverter 73. The output of the inverter 73 is connected to one input of a two-input NAND 74. To the other input of the NAND 74, initial signal INT is applied that is turned to be low level for a fixed time right after the power is switched on and then turned to be high level. The output of the NAND 74 is connected to a node NC0, and control signal YFD is outputted to the node NC0.